

isc Silicon NPN Power Transistor

2SD844

DESCRIPTION

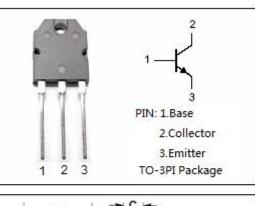
- Collector-Emitter Breakdown Voltage-
- : V_{(BR)CEO}= 50V (Min)
- Low Collector-Emitter Saturation Voltage : V_{CE(sat)}= 0.4V (Max)@I_C= 4A
- High Collector Power Dissipation : P_C = 60W @T_C=25 °C
- Complement to Type 2SB754
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

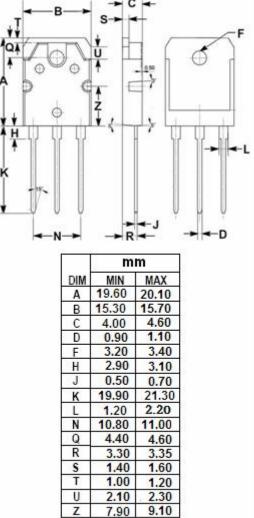
APPLICATIONS

- High current switching applications
- Power amplifier applications

ABSOLUT	FE MAXIMUM RATINGS(Ta=25℃)

PARAMETER	VALUE	UNIT	
Collector-Base Voltage	50	V	
Collector-Emitter Voltage	50	V	
Emitter-Base Voltage	5	V	
Collector Current-Continuous	7	A	
Emitter Current-Continuous	7	A	
Collector Power Dissipation @ $T_a=25^{\circ}C$	2.5	W	
Collector Power Dissipation @ Tc=25℃	60	vv	
unction Temperature 150		°C	
Storage Temperature Range	-55~150	°C	
	Collector-Base Voltage Collector-Emitter Voltage Emitter-Base Voltage Collector Current-Continuous Emitter Current-Continuous Collector Power Dissipation @ $T_a=25^{\circ}C$ Collector Power Dissipation @ $T_c=25^{\circ}C$ Junction Temperature	Collector-Base Voltage50Collector-Emitter Voltage50Emitter-Base Voltage5Collector Current-Continuous7Emitter Current-Continuous7Collector Power Dissipation @ Ta=25°C2.5Collector Power Dissipation @ Tc=25°C60Junction Temperature150	





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ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA ; I _B = 0	50			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 1mA ; I _C = 0	5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 4A; I _B = 0.4A		0.2	0.4	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 4A ; V _{CE} = 1V		0.9	1.2	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 50V ; I _E = 0			10	μA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V ; I _C = 0			10	μA
h _{FE -1}	DC Current Gain	I _C = 1A ; V _{CE} = 1V	70		240	
h _{FE -2}	DC Current Gain	I _C = 4A ; V _{CE} = 1V	30			

h_{FE-1} Classifications

0	Y	
70-140	120-240	

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